



INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Staple

of

Complete If Known

Application Number	10/670,928
Filing Date	September 25, 2003
First Named Inventor	Chun-Li Liu et al.
Group Art Unit	2812
Examiner Name	Unassigned
Attorney Docket Number	SC12851ZP

U. S. PATENT DOCUMENTS

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.*	Document Number Number + Kind Code* (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
Dle	B1	5,534,713	07/09/1996	Ismail et al.	—
	B2	5,846,857	12/08/1998	Ju	—
	B3	5,943,565	08/24/1999	Ju	—
	B4	5,998,807	12/07/1999	Lustig et al.	—
	B5	6,059,895	05/09/2000	Chu et al.	—
	B6	6,124,627	09/26/2000	Rodder et al.	—
	B7	2001/0048119 A1	12/06/2001	Mizuno et al.	—
	B8	6,339,232 B1	01/15/2002	Takagi	—
Dle	B9	6,621,131 B2	09/16/2003	Murthy et al.	—
Dle	B10	6,638,802 B1	10/28/2003	Hwang et al.	—

FOREIGN PATENT DOCUMENTS

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Case No. *	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T?
<i>Dly</i>	B12	Jung et al., "Implementation of Both High-Hole and Electron Mobility in Strained Si/Strained Si _x Ge _y on Relaxed Si _{1-x} Ge _x (x<y) Virtual Substrate," <i>IEEE Electron Device Letters</i> , Vol. 24, No. 7, July 2003, pp. 460-462.	
	B13	Tezuka et al., "Ultrathin Body SiGe-on-Insulator pMOSFETs with High-Mobility SiGe Surface Channels," <i>IEEE Transactions on Electron Devices</i> , Vol. 50, No. 5, May 2003, pp. 1328-1333.	

Examiner Signature	Dee	Date Considered	4/2005
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 603. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See *Kinds of U.S. Patent Documents*. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English Language Translation is attached.

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <small>(use as many sheets as necessary)</small>				<i>Complete if Known</i>	
				Application Number	10/670928
				Filing Date	
				First Named Inventor	Chun-Li Liu
				Group Art Unit	2818
				Examiner Name	D. LE
Sheet	of	Attorney Docket Number	SC12851ZP		

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
DL	AA	5,461,243	10/24/1995	Ek et al.	—
	AB	5,759,898	06/02/1998	Ek et al.	—
	AC	6,369,438 B1	04/09/2002	Sugiyama et al.	—
	AD	2003/0034529 A1	10/08/2002	Fitzgerald	—
	AE	2003/0013305 A1	01/16/2003	Sugii et al.	—
	AF	6,524,935 B1	02/25/2003	Canaperi et al.	—
DL	AG	2003/0040160 A1	02/27/2003	Huang et al.	—

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ² (if known)				
DL	AH	JP 2000243946	12/06/1999	Naoharu et al.	—	Yes/Abstract
	AI	WO 02/33746 A1	04/22/2002	Chu et al.	—	

NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				
DL	AJ	Chi et al., "Electrically active defects in surface preamorphized and subsequently RTP-annealed Si and the effect of titanium silicidation," <i>Proc. 1998 5th International Conference on Solid-State and Integrated Circuit Technology</i> , October 21, 1998, Beijing, China, p. 324-327.				✓
	AK	Fahey et al., "Point defects and dopant diffusion in silicon," <i>Reviews of Modern Physics</i> , April 1989, Vol. 61, No. 2, pp. 289-384.				
	AL	Lee et al., "Sub-30 nm P+ abrupt junction formation in Strained Si/Si _x -Ge _{1-x} MOS device," <i>Technical Digest of the International Electron Devices Meeting</i> , December 8, 2002, pp. 379-81.				
	AM	LeGoues et al., "Kinetics and Mechanism of Oxidation of SiGe: Dry Versus Wet Oxidation," <i>Applied Physics Letters</i> , February 13, 1989, Vol. 54, No. 7, pp. 644-646.				
	AN	LeGoues et al., "Oxidation Studies of SiGe," <i>Journal of Applied Physics</i> , February 15, 1989, Vol. 65, No. 4, pp. 1724-1728.				
	AO	Lim et al., "Dry Thermal Oxidation of a Graded SiGe Layer," <i>Applied Physics Letters</i> , November 26, 2001, Vol. 79, No. 22, pp. 3606-3608.				
	AP	Sawano et al., "Relaxation Enhancement of SiGe Thin Layers by Ion Implantation into Si Substrates," <i>IEEE</i> , 2002, pp. 403-404.				
	AQ	Tezuka et al., "Dislocation-free Formation of Relaxed SiGe-on-insulator Layers," <i>Applied Physics Letters</i> , May 13, 2002, Vol. 80, No. 19, pp. 3560-3562.				
	AR	Tezuka et al., "Fabrication of Strained Si on an Ultrathin SiGe-on-insulator Virtual Substrate with a High-Ge Fraction," <i>Applied Physics Letters</i> , September 17, 2001, Vol. 79, No. 12, pp. 1798-1800.				
DL	AS	Vyatkin et al., "Ion Beam Induced Strain Relaxation in Pseudomorphic Epitaxial SiGe Layers," <i>IEEE</i> , 2000, pp. 70-72.				

Examiner Signature	DL	Date Considered	Feb - 2005
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